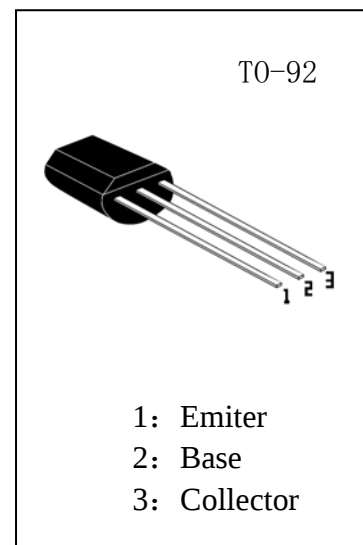


GENERAL PURPOSE TRANSISTOR

- $V_{ce0} = -40V$
- $P_c = 625mW$
- 与 2N3904 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	-40	V
Collector-Emitter Voltage	V_{ceo}	-40	V
Emitter-Base Voltage	V_{ebo}	-6	V
Collector Current	I_c	-200	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$


电性能(Electrical Characteristic) $T_a = 25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c = -10\mu A, I_e = 0$	-40			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c = -1mA, I_b = 0$	-40			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e = -10\mu A, I_c = 0$	-6			V
I_{cbo}	Collector Cutoff Current	$V_{cb} = -35V, I_e = 0$			-100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb} = -3V, I_c = 0$			-50	nA
I_{cex}	Collector Cutoff Current	$V_{ce} = -30V, V_{eb} = -3V$			-50	nA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c = -10mA, I_b = -1mA$			-0.25	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c = -50mA, I_b = -5mA$			-0.4	V
$V_{be(sat)1}$	Base-Emitter Saturation Voltage	$I_c = -10mA, I_b = -1mA$			-0.85	V
$V_{be(sat)2}$	Base-Emitter Saturation Voltage	$I_c = -50mA, I_b = -5mA$			-0.95	V
Hfe1	DC Current Gain	$V_{ce} = -1V, I_c = -0.1mA$	60			
Hfe2	DC Current Gain	$V_{ce} = -1V, I_c = -1mA$	80			
Hfe3	DC Current Gain	$V_{ce} = -1V, I_c = -10mA$	80		300	
Hfe4	DC Current Gain	$V_{ce} = -1V, I_c = -50mA$	60			
Hfe5	DC Current Gain	$V_{ce} = -1V, I_c = -100mA$	30			
Cob	Output Capacitance	$V_{cb} = -5V, I_e = 0, f = 100kHz$			4.5	PF
fT	Current Gain-Bandwidth product	$V_{ce} = -20V, I_c = -10mA,$	250			MHz

CLASS	B	C	D	E
Hfe3	80-100	100-200	200-300	300-400